

Docket No.: 21302/0203830-US0
(PATENT)

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Euijoon Yoon et al.

Application No.: 10/563,854

Confirmation No.: 3828

Filed: June 9, 2006

Art Unit: 2823

For: GROWTH METHOD FOR NITRIDE
SEMICONDUCTOR EPITAXIAL LAYERS

Examiner: Maldonado, J. J.

RESPONSE TO FINAL OFFICE ACTION (37 C.F.R. § 1.116)

MS AF
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

INTRODUCTORY COMMENTS

In response to the Final Office Action dated July 8, 2008, and with the Examiner's approval, please amend the above-identified U.S. patent application as follows:

Remarks/Arguments begin on page 2 of this paper.

OK TO ENTER: /J.M./